

Integrated Synthesizer and VCO

ADF4360-8

FEATURES

Output frequency range: 65 MHz to 400 MHz
3.0 V to 3.6 V power supply
1.8 V logic compatibility
Integer-N synthesizer
Programmable output power level
3-wire serial interface
Digital lock detect
Hardware and software power-down mode

APPLICATIONS

System clock generation Test equipment Wireless LANs CATV equipment

GENERAL DESCRIPTION

The ADF4360-8 is an integrated integer-N synthesizer and voltage controlled oscillator (VCO). The ADF4360-8 center frequency is set by external inductors. This allows a frequency range of between 65 MHz to 400 MHz.

Control of all the on-chip registers is through a simple 3-wire interface. The device operates with a power supply ranging from $3.0\,\mathrm{V}$ to $3.6\,\mathrm{V}$ and can be powered down when not in use.

FUNCTIONAL BLOCK DIAGRAM

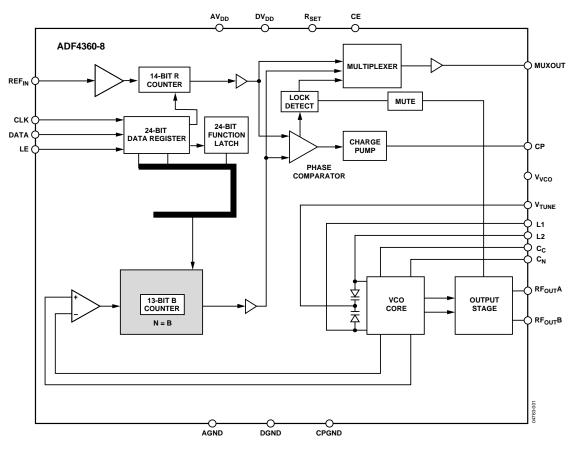


Figure 1.

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REVISION HISTORY

10/04—Revision 0: Initial Version

SPECIFICATIONS1

 $AV_{DD} = DV_{DD} = V_{VCO} = 3.3~V~\pm~10\%; AGND = DGND = 0~V; T_{A} = T_{MIN}~to~T_{MAX}, unless otherwise~noted.$

Table 1.

| Parameter | B Version | Unit | Conditions/Comments |
|--|------------------------|---------------|--|
| REF _{IN} CHARACTERISTICS | | | |
| REF _{IN} Input Frequency | 10/250 | MHz min/max | For f < 10 MHz, use a dc-coupled CMOS-compatible square wave, slew rate > 21 V/µs. |
| REF _{IN} Input Sensitivity | 0.7/AV _{DD} | V p-p min/max | AC-coupled. |
| | 0 to AV _{DD} | V max | CMOS-compatible. |
| REF _{IN} Input Capacitance | 5.0 | pF max | |
| REF _{IN} Input Current | ±60 | μA max | |
| PHASE DETECTOR | | | |
| Phase Detector Frequency ² | 8 | MHz max | |
| CHARGE PUMP | | | |
| I _{CP} Sink/Source ³ | | | With $R_{SET} = 4.7 \text{ k}\Omega$. |
| High Value | 2.5 | mA typ | |
| Low Value | 0.312 | mA typ | |
| R _{SET} Range | 2.7/10 | kΩ | |
| I _{CP} Three-State Leakage Current | 0.2 | nA typ | |
| Sink and Source Current Matching | 2 | % typ | $1.25 \text{ V} \le \text{V}_{CP} \le 2.5 \text{ V}.$ |
| I _{CP} vs. V _{CP} | 1.5 | % typ | $1.25 \text{ V} \le \text{V}_{CP} \le 2.5 \text{ V}.$ |
| I _{CP} vs. Temperature | 2 | % typ | $V_{CP} = 2.0 \text{ V}.$ |
| LOGIC INPUTS | | | |
| V _{INH} , Input High Voltage | 1.5 | V min | |
| V _{INL} , Input Low Voltage | 0.6 | V max | |
| I _{INH} /I _{INL} , Input Current | ±1 | μA max | |
| C _{IN} , Input Capacitance | 3.0 | pF max | |
| LOGIC OUTPUTS | | | |
| V _{он} , Output High Voltage | DV _{DD} - 0.4 | V min | CMOS output chosen. |
| Iон, Output High Current | 500 | μA max | |
| V _{OL} , Output Low Voltage | 0.4 | V max | $I_{OL} = 500 \mu A.$ |
| POWER SUPPLIES | | | |
| AV_DD | 3.0/3.6 | V min/V max | |
| DV_{DD} | AV_{DD} | | |
| V_{VCO} | AV_{DD} | | |
| AI_{DD}^4 | 5 | mA typ | |
| DI_{DD}^4 | 2.5 | mA typ | |
| l _{VCO} ^{4, 5} | 12.0 | mA typ | $I_{CORE} = 5 \text{ mA}.$ |
| I _{RFOUT} ⁴ | 3.5 to 11.0 | mA typ | RF output stage is programmable. |
| Low Power Sleep Mode⁴ | 7 | μA typ | |

Specifications continued on next page.

Footnotes on next page.

| Parameter | B Version | Unit | Conditions/Comments |
|--|------------------|-------------|--|
| RF OUTPUT CHARACTERISTICS ⁵ | | | |
| Maximum VCO Output Frequency | 400 | MHz | I _{CORE} = 5 mA. Depending on L. See the Choosing the Correct Inductance Value section. |
| Minimum VCO Output Frequency | 65 | MHz | |
| VCO Output Frequency | 88/108 | MHz min/max | L1, L2 = 270 nH. See the Choosing the Correct Inductance Value section for other frequency values. |
| VCO Frequency Range | 1.2 | Ratio | F _{MAX} / F _{MIN} |
| VCO Sensitivity | 2 | MHz/V typ | L1, L2 = 270 nH. See the Choosing the Correct Inductance Value section for other sensitivity values. |
| Lock Time ⁶ | 400 | μs typ | To within 10 Hz of final frequency. |
| Frequency Pushing (Open Loop) | 0.24 | MHz/V typ | |
| Frequency Pulling (Open Loop) | 10 | Hz typ | Into 2.00 VSWR load. |
| Harmonic Content (Second) | -16 | dBc typ | |
| Harmonic Content (Third) | -21 | dBc typ | |
| Output Power ^{5, 7} | -9/0 | dBm typ | Using tuned load, programmable in 3 dB steps. See Table 7. |
| Output Power ^{5, 8} | -14/-9 | dBm typ | Using 50 Ω resistors to V _{VCO} , programmable in 3 dB steps. See Table 7. |
| Output Power Variation | ±3 | dB typ | |
| VCO Tuning Range | 1.25/2.5 | V min/max | |
| NOISE CHARACTERISTICS ⁵ | | | |
| VCO Phase Noise Performance9 | -120 | dBc/Hz typ | @ 100 kHz offset from carrier. |
| | -139 | dBc/Hz typ | @ 800 kHz offset from carrier. |
| | -140 | dBc/Hz typ | @ 3 MHz offset from carrier. |
| | -142 | dBc/Hz typ | @ 10 MHz offset from carrier. |
| Synthesizer Phase Noise Floor ¹⁰ | -160 | dBc/Hz typ | @ 200 kHz PFD frequency. |
| | -150 | dBc/Hz typ | @ 1 MHz PFD frequency. |
| | -142 | dBc/Hz typ | @ 8 MHz PFD frequency. |
| Phase Noise Figure of Merit10 | -209 | dBc/Hz typ | |
| In-Band Phase Noise11,12 | -102 | dBc/Hz typ | @ 1 kHz offset from carrier. |
| RMS Integrated Phase Error ¹³ | 0.09 | Degrees typ | 100 Hz to 100 kHz. |
| Spurious Signals due to PFD Frequency ^{12, 14} | -75 | dBc typ | |
| Level of Unlocked Signal with MTLD Enabled | -7 0 | dBm typ | |

¹ Operating temperature range is -40°C to +85°C.

² Guaranteed by design. Sample tested to ensure compliance.

³ l_{CP} is internally modified to maintain constant loop gain over the frequency range.

 $^{^{4}}$ T_A = 25°C; AV_{DD} = DV_{DD} = V_{VCO} = 3.3 V.

⁵ Unless otherwise stated, these characteristics are guaranteed for VCO core power = 5 mA. L1, L2 = 270 nH, 470 Ω resistors to GND in parallel with L1, L2.

⁶ Jumping from 88 MHz to 108 MHz. PFD frequency = 200 kHz; loop bandwidth = 10 kHz.

 $^{^7}$ For more detail on using tuned loads, see Output Matching section. 8 Using 50 Ω resistors to V_{VCO} , into a 50 Ω load.

⁹ The noise of the VCO is measured in open-loop conditions.

¹⁰ The synthesizer phase noise floor is estimated by measuring the in-band phase noise at the output of the VCO and subtracting 20 log N (where N is the N divider value). The phase noise figure of merit subtracts 10 log (PFD frequency).

The phase noise is measured with the EVAL-ADF4360-xEB1 Evaluation Board and the HP 8562E Spectrum Analyzer. The Spectrum Analyzer provides the REFIN for the

synthesizer; offset frequency = 1 kHz.

 $^{^{12}\,}f_{REFIN} = 10$ MHz; $f_{PFD} = 200$ kHz; N = 1000; Loop B/W = 10 kHz.

 $^{^{13}}$ f_{REFIN} = 10 MHz; f_{PFD} = 1 MHz; N = 120; Loop B/W = 100 kHz.

¹⁴ The spurious signals are measured with the EVAL-ADF4360-xEB1 Evaluation Board and the HP 8562E Spectrum Analyzer. The Spectrum Analyzer provides the REFIN for the synthesizer; f_{REFOUT} = 10 MHz @ 0 dBm.

TIMING CHARACTERISTICS

 $AV_{DD} = DV_{DD} = V_{VCO} = 3.3 \ V \pm 10\%; AGND = DGND = 0 \ V; 1.8 \ V \ and \ 3 \ V \ logic \ levels \ used; T_A = T_{MIN} \ to \ T_{MAX}, unless \ otherwise \ noted.$

Table 2.

| Parameter | Limit at T _{MIN} to T _{MAX} (B Version) | Unit | Test Conditions/Comments |
|-----------------------|---|--------|--------------------------|
| t ₁ | 20 | ns min | LE Setup Time |
| t_2 | 10 | ns min | DATA to CLOCK Setup Time |
| t ₃ | 10 | ns min | DATA to CLOCK Hold Time |
| t ₄ | 25 | ns min | CLOCK High Duration |
| t ₅ | 25 | ns min | CLOCK Low Duration |
| t ₆ | 10 | ns min | CLOCK to LE Setup Time |
| t ₇ | 20 | ns min | LE Pulse Width |

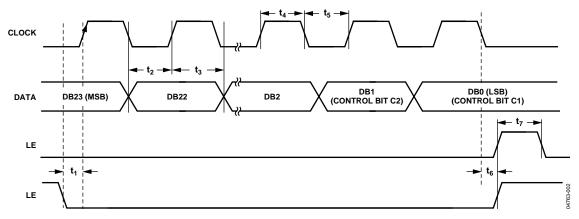


Figure 2. Timing Diagram

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 3.

| 14016 51 | 1 |
|--------------------------------------|--|
| Parameter | Rating |
| AV _{DD} to GND ¹ | −0.3 V to +3.9 V |
| AV_{DD} to DV_{DD} | -0.3 V to +0.3 V |
| V _{vco} to GND | −0.3 V to +3.9 V |
| V_{VCO} to AV_{DD} | -0.3 V to +0.3 V |
| Digital I/O Voltage to GND | $-0.3 \text{ V to V}_{DD} + 0.3 \text{ V}$ |
| Analog I/O Voltage to GND | $-0.3 \text{ V to V}_{DD} + 0.3 \text{ V}$ |
| REF _{IN} to GND | $-0.3 \text{ V to V}_{DD} + 0.3 \text{ V}$ |
| Operating Temperature Range | -40°C to + 85°C |
| Storage Temperature Range | −65°C to +150°C |
| Maximum Junction Temperature | 150°C |
| CSP θ_{JA} Thermal Impedance | |
| Paddle Soldered | 50°C/W |
| Paddle Not Soldered | 88°C/W |
| Lead Temperature, Soldering | |
| Vapor Phase (60 sec) | 215°C |
| Infrared (15 sec) | 220°C |
| | |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

This device is a high performance RF integrated circuit with an ESD rating of <1 kV, and it is ESD sensitive. Proper precautions should be taken for handling and assembly.

TRANSISTOR COUNT

12543 (CMOS) and 700 (Bipolar)

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



 $^{^{1}}$ GND = AGND = DGND = 0 V.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

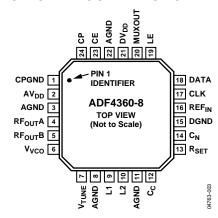


Figure 3. Pin Configuration

Table 4. Pin Function Descriptions

| Pin No. | Mnemonic | Function |
|--------------|---------------------|--|
| 1 | CPGND | Charge Pump Ground. This is the ground return path for the charge pump. |
| 2 | AV_DD | Analog Power Supply. This ranges from 3.0 V to 3.6 V. Decoupling capacitors to the analog ground plane should be placed as close as possible to this pin. AV_{DD} must have the same value as DV_{DD} . |
| 3, 8, 11, 22 | AGND | Analog Ground. This is the ground return path of the prescaler and VCO. |
| 4 | RF _{OUT} A | VCO Output. The output level is programmable from 0 dBm to –9 dBm. See the Output Matching section for a description of the various output stages. |
| 5 | RF _{OUT} B | VCO Complementary Output. The output level is programmable from 0 dBm to –9 dBm. See the Output Matching section for a description of the various output stages. |
| 6 | V _{vco} | Power Supply for the VCO. This ranges from 3.0 V to 3.6 V. Decoupling capacitors to the analog ground plane should be placed as close as possible to this pin. V_{VCO} must have the same value as AV_{DD} . |
| 7 | V _{TUNE} | Control Input to the VCO. This voltage determines the output frequency and is derived from filtering the CP output voltage. |
| 9 | L1 | An external inductor to AGND should be connected to this pin to set the ADF4360-8 output frequency. L1 and L2 need to be the same value. A 470 Ω resistor should be added in parallel to AGND. |
| 10 | L2 | An external inductor to AGND should be connected to this pin to set the ADF4360-8 output frequency. L1 and L2 need to be the same value. A 470 Ω resistor should be added in parallel to AGND. |
| 12 | Cc | Internal Compensation Node. This pin must be decoupled to ground with a 10 nF capacitor. |
| 13 | R _{SET} | Connecting a resistor between this pin and CP_{GND} sets the maximum charge pump output current for the synthesizer. The nominal voltage potential at the R_{SET} pin is 0.6 V. The relationship between I_{CP} and R_{SET} is $I_{CPmax} = \frac{11.75}{R_{SET}}$ |
| | | where $R_{SET} = 4.7 \text{ k}\Omega$, $I_{CPmax} = 2.5 \text{ mA}$. |
| 14 | C _N | Internal Compensation Node. This pin must be decoupled to V_{VCO} with a 10 μF capacitor. |
| 15 | DGND | Digital Ground. |
| 16 | REF _{IN} | Reference Input. This is a CMOS input with a nominal threshold of $V_{DD}/2$ and a dc equivalent input resistance of 100 k Ω (see Figure 16). This input can be driven from a TTL or CMOS crystal oscillator, or it can be ac-coupled. |
| 17 | CLK | Serial Clock Input. This serial clock is used to clock in the serial data to the registers. The data is latched into the 24-bit shift register on the CLK rising edge. This input is a high impedance CMOS input. |
| 18 | DATA | Serial Data Input. The serial data is loaded MSB first with the two LSBs being the control bits. This input is a high impedance CMOS input. |
| 19 | LE | Load Enable, CMOS Input. When LE goes high, the data stored in the shift registers is loaded into one of the four latches, and the relevant latch is selected using the control bits. |
| 20 | MUXOUT | This multiplexer output allows either the lock detect, the scaled RF, or the scaled reference frequency to be accessed externally. |
| 21 | DV_{DD} | Digital Power Supply. This ranges from 3.0 V to 3.6 V. Decoupling capacitors to the digital ground plane should be placed as close as possible to this pin. DV_{DD} must have the same value as AV_{DD} . |
| 23 | CE | Chip Enable. A logic low on this pin powers down the device and puts the charge pump into three-state mode. Taking the pin high powers up the device depending on the status of the power-down bits. |
| 24 | СР | Charge Pump Output. When enabled, this provides $\pm l_{\mathbb{C}^p}$ to the external loop filter, which in turn drives the internal VCO. |

TYPICAL PERFORMANCE CHARACTERISTICS

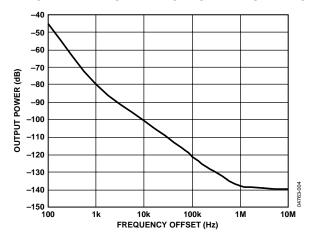


Figure 4. Open-Loop VCO Phase Noise, L1, L2 = 560 nH

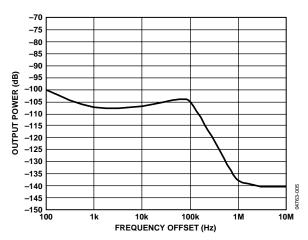


Figure 5. VCO Phase Noise, 65 MHz, 1 MHz PFD, 100 kHz Loop Bandwidth

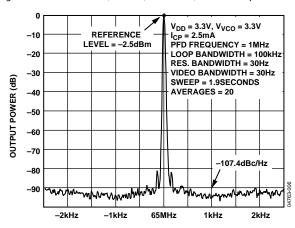


Figure 6. Close-In Phase Noise at 65 MHz (1 MHz Channel Spacing)

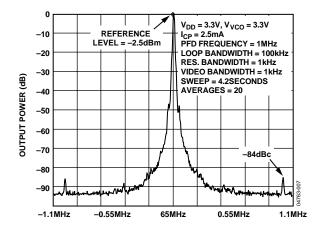


Figure 7. Reference Spurs at 65 MHz (1 MHz Channel Spacing, 100 kHz Loop Bandwidth)

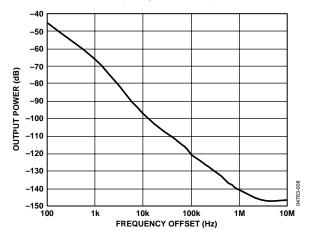


Figure 8. Open-Loop VCO Phase Noise, L1, L2 = 110 nH

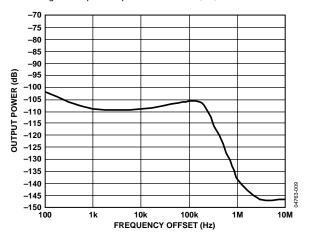


Figure 9. VCO Phase Noise, 160 MHz, 1 MHz PFD, 100 kHz Loop Bandwidth

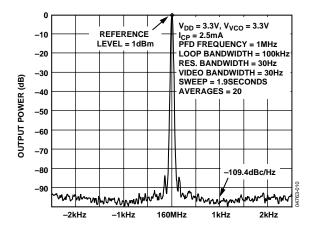


Figure 10. Close-In Phase Noise at 160 MHz (1 MHz Channel Spacing)

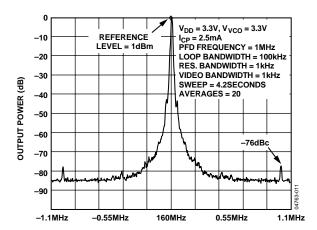


Figure 11. Reference Spurs at 160 MHz (1 MHz Channel Spacing, 100 kHz Loop Bandwidth)

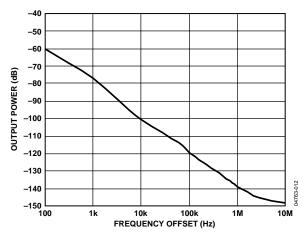


Figure 12. Open-Loop VCO Phase Noise, L1, L2 = 18 nH

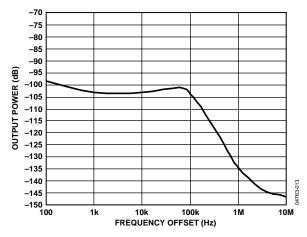


Figure 13. VCO Phase Noise, 400 MHz, 1 MHz PFD, 100 kHz Loop Bandwidth

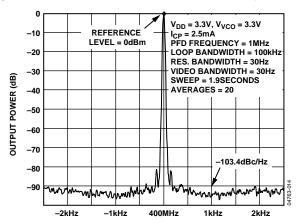


Figure 14. Close-In Phase Noise at 400 MHz (1 MHz Channel Spacing)

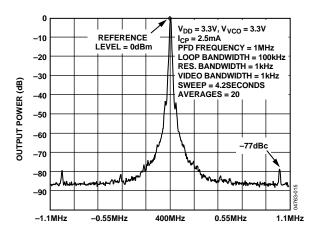


Figure 15. Reference Spurs at 400 MHz (1 MHz Channel Spacing, 100 kHz Loop Bandwidth)

CIRCUIT DESCRIPTION

REFERENCE INPUT SECTION

The reference input stage is shown in Figure 16. SW1 and SW2 are normally closed switches. SW3 is normally open. When power-down is initiated, SW3 is closed, and SW1 and SW2 are opened. This ensures that there is no loading of the REF $_{\rm IN}$ pin on power-down.

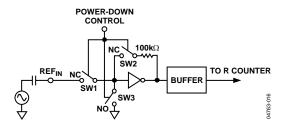


Figure 16. Reference Input Stage

N COUNTER

The CMOS N counter allows a wide division ratio in the PLL feedback counter. The counters are specified to work when the VCO output is 400 MHz or less. To avoid confusion, this is referred to as the B counter. It makes it possible to generate output frequencies that are spaced only by the reference frequency divided by *R*. The VCO frequency equation is

$$f_{VCO} = B \times f_{REFIN} / R$$

where:

 f_{VCO} is the output frequency of the VCO. *B* is the preset divide ratio of the binary 13-bit counter (3 to 8191). f_{REFIN} is the external reference frequency oscillator.

R COUNTER

The 14-bit R counter allows the input reference frequency to be divided down to produce the reference clock to the phase frequency detector (PFD). Division ratios from 1 to 16,383 are allowed.

PFD AND CHARGE PUMP

The PFD takes inputs from the R counter and N counter (N = BP + A) and produces an output proportional to the phase and frequency difference between them. Figure 17 is a simplified schematic. The PFD includes a programmable delay element that controls the width of the antibacklash pulse. This pulse ensures that there is no dead zone in the PFD transfer function and minimizes phase noise and reference spurs. Two bits in the R counter latch, ABP2 and ABP1, control the width of the pulse (see Table 9).

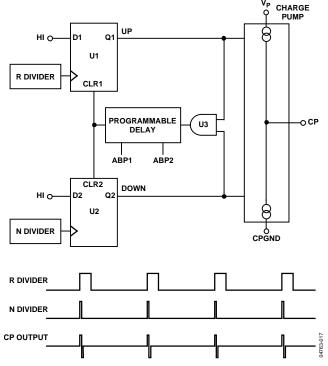


Figure 17. PFD Simplified Schematic and Timing (In Lock)

MUXOUT AND LOCK DETECT

The output multiplexer on the ADF4360 family allows the user to access various internal points on the chip. The state of MUXOUT is controlled by M3, M2, and M1 in the function latch. The full truth table is shown in Table 7. Figure 18 shows the MUXOUT section in block diagram form.

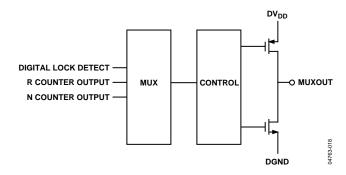


Figure 18. MUXOUT Circuit

Lock Detect

MUXOUT can be programmed for one type of lock detect. Digital lock detect is active high. When LDP in the R counter latch is set to 0, digital lock detect is set high when the phase error on three consecutive phase detector cycles is less than 15 ns.

With LDP set to 1, five consecutive cycles of less than 15 ns phase error are required to set the lock detect. It stays set high until a phase error of greater than 25 ns is detected on any subsequent PD cycle.

INPUT SHIFT REGISTER

The ADF4360 family's digital section includes a 24-bit input shift register, a 14-bit R counter, and an 18-bit N counter comprised of a 5-bit A counter and a 13-bit B counter. Data is clocked into the 24-bit shift register on each rising edge of CLK. The data is clocked in MSB first. Data is transferred from the shift register to one of four latches on the rising edge of LE. The destination latch is determined by the state of the two control bits (C2, C1) in the shift register. These are the two LSBs, DB1 and DB0, shown in Figure 2.

The truth table for these bits is shown in Table 5. Table 6 shows a summary of how the latches are programmed. Note that the test modes latch is used for factory testing and should not be programmed by the user.

Table 5. C2 and C1 Truth Table

| Conti | ol Bits | |
|-------|---------|------------------|
| C2 | C1 | Data Latch |
| 0 | 0 | Control Latch |
| 0 | 1 | R Counter |
| 1 | 0 | N Counter (B) |
| 1 | 1 | Test Modes Latch |

VCO

The VCO core in the ADF4360 family uses eight overlapping bands, as shown in Figure 19, to allow a wide frequency range to be covered without a large VCO sensitivity (K_V) and resultant poor phase noise and spurious performance.

The correct band is chosen automatically by the band select logic at power-up or whenever the N counter latch is updated. It is important that the correct write sequence be followed at power-up. This sequence is

- 1. R counter latch
- 2. Control latch
- 3. N counter latch

During band select, which takes five PFD cycles, the VCO V_{TUNE} is disconnected from the output of the loop filter and connected to an internal reference voltage.

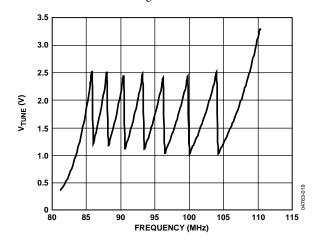


Figure 19. Frequency vs. V_{TUNE} , ADF4360-8, L1 and L2 = 270 nH

The R counter output is used as the clock for the band select logic and should not exceed 1 MHz. A programmable divider is provided at the R counter input to allow division by 1, 2, 4, or 8 and is controlled by Bits BSC1 and BSC2 in the R counter latch. Where the required PFD frequency exceeds 1 MHz, the divide ratio should be set to allow enough time for correct band selection.

After band selection, normal PLL action resumes. The value of $K_{\rm V}$ is determined by the value of inductors used (see the Choosing the Correct Inductance Value section). The ADF4360 family contains linearization circuitry to minimize any variation of the product of I_{CP} and $K_{\rm V}$.

The operating current in the VCO core is programmable in four steps: 2.5 mA, 5 mA, 7.5 mA, and 10 mA. This is controlled by Bits PC1 and PC2 in the control latch.

OUTPUT STAGE

The RFouth and RFouth pins of the ADF4360 family are connected to the collectors of an NPN differential pair driven by buffered outputs of the VCO, as shown in Figure 20. To allow the user to optimize the power dissipation versus the output power requirements, the tail current of the differential pair is programmable via Bits PL1 and PL2 in the control latch. Four current levels may be set: 3.5 mA, 5 mA, 7.5 mA, and 11 mA. These levels give output power levels of -9~dBm, -6~dBm, -3~dBm, and 0 dBm, respectively, using the correct shunt inductor to $V_{\rm DD}$ and ac coupling into a 50 Ω load. Alternatively, both outputs can be combined in a 1 + 1:1 transformer or a 180° microstrip coupler (see the Output Matching section).

If the outputs are used individually, the optimum output stage consists of a shunt inductor to $V_{\rm DD}\!.$

Another feature of the ADF4360 family is that the supply current to the RF output stage is shut down until the part achieves lock as measured by the digital lock detect circuitry. This is enabled by the Mute-Till-Lock Detect (MTLD) bit in the control latch.

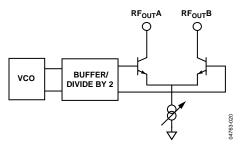


Figure 20. Output Stage ADF4360-8

LATCH STRUCTURE

Table 6 shows the three on-chip latches for the ADF4360 family. The two LSBs decide which latch is programmed.

Table 6. Latch Structure

CONTROL LATCH

| RESERVED | RESERVED | ≥ ≥ | POWER- DOWN 1 | | JRREN | - | | URREN | | OUT POV LE\ | | MUTE-TIL- LD | CP GAIN | CP THREE- STATE | PHASE DETECTOR POLARITY | | MUXOU | | COUNTER RESET | CO POV LE\ | VER | CON | - |
|----------|----------|------|------------------|------|-------|------|------|-------|------|-------------------|------|-----------------|---------|-----------------------|-------------------------------|-----|-------|-----|------------------|------------------|-----|--------|--------|
| DB23 | DB22 | DB21 | DB20 | DB19 | DB18 | DB17 | DB16 | DB15 | DB14 | DB13 | DB12 | DB11 | DB10 | DB9 | DB8 | DB7 | DB6 | DB5 | DB4 | DB3 | DB2 | DB1 | DB0 |
| RSV | RSV | PD2 | PD1 | CPI6 | CPI5 | CPI4 | CPI3 | CPI2 | CPI1 | PL2 | PL1 | MTLD | CPG | СР | PDP | М3 | M2 | M1 | CR | PC2 | PC1 | C2 (0) | C1 (0) |

N COUNTER LATCH

| RESERVED | RESERVED | CP GAIN | | | | | | 13-BIT | B COU | NTER | | | | | | | | RESE | RVED | | | CON' BI | - |
|----------|----------|---------|------|------|------|------|------|--------|-------|------|------|------|------|-----|-----|-----|-----|------|------|-----|-----|------------|--------|
| DB23 | DB22 | DB21 | DB20 | DB19 | DB18 | DB17 | DB16 | DB15 | DB14 | DB13 | DB12 | DB11 | DB10 | DB9 | DB8 | DB7 | DB6 | DB5 | DB4 | DB3 | DB2 | DB1 | DB0 |
| RSV | RSV | CPG | B13 | B12 | B11 | B10 | В9 | В8 | B7 | В6 | В5 | В4 | В3 | B2 | B1 | RSV | RSV | RSV | RSV | RSV | RSV | C2 (1) | C1 (0) |

R COUNTER LATCH

| RESERVED | RESERVED | _ | ECT | TEST MODE BIT | LOCK DETECT PRECISION | AN BACK PUL WIE | LASH .SE | | | | | 1 | 4-BIT R | EFERE | ENCE C | OUNT | ER | | | | | | TROL TS |
|----------|----------|------|------|---------------------|-----------------------------|--------------------------|-------------|------|------|------|------|------|---------|-------|--------|------|-----|-----|-----|-----|-----|--------|------------|
| DB23 | DB22 | DB21 | DB20 | DB19 | DB18 | DB17 | DB16 | DB15 | DB14 | DB13 | DB12 | DB11 | DB10 | DB9 | DB8 | DB7 | DB6 | DB5 | DB4 | DB3 | DB2 | DB1 | DB0 |
| RSV | RSV | BSC2 | BSC1 | ТМВ | LDP | ABP2 | ABP1 | R14 | R13 | R12 | R11 | R10 | R9 | R8 | R7 | R6 | R5 | R4 | R3 | R2 | R1 | C2 (0) | C1 (1) |

Table 7. Control Latch

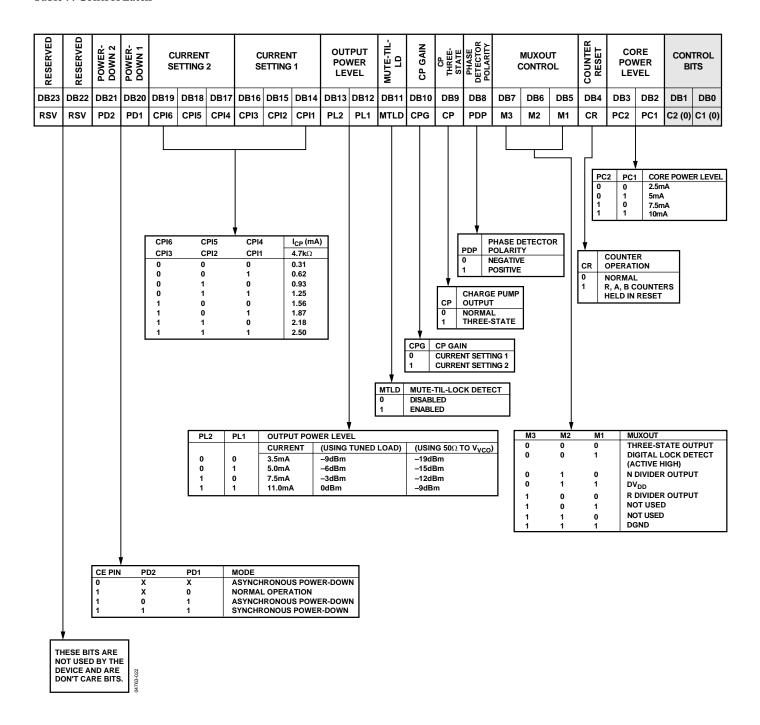


Table 8. N Counter Latch

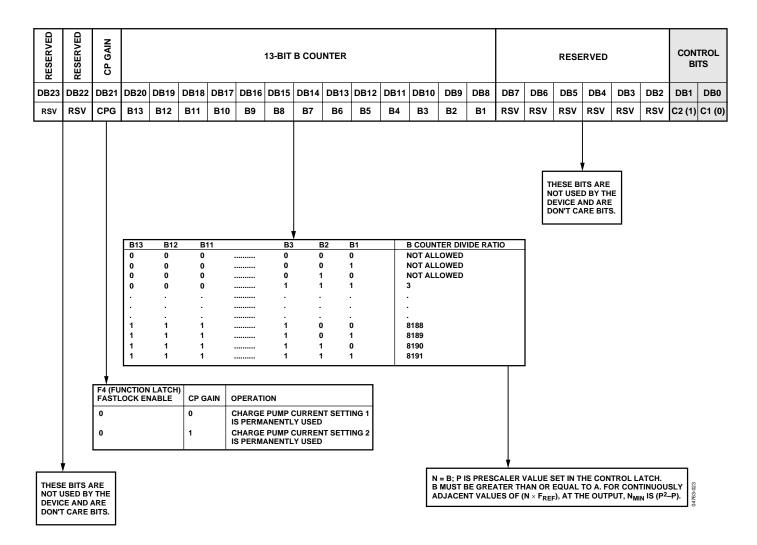
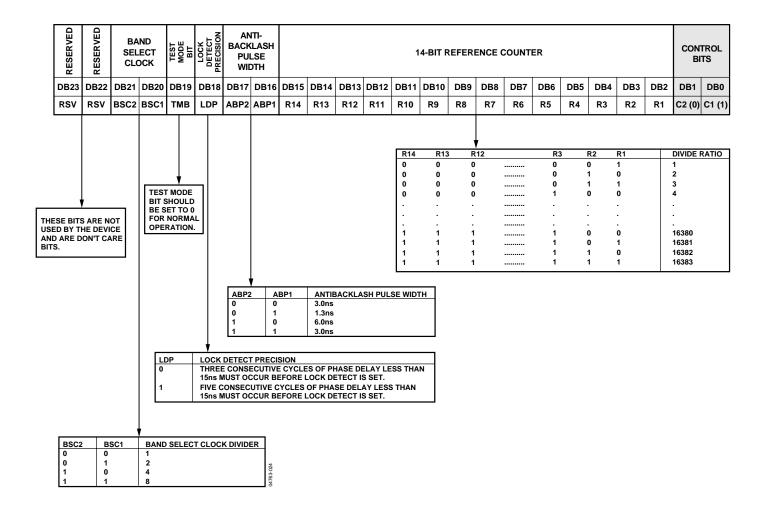


Table 9. R Counter Latch



CONTROL LATCH

With (C2, C1) = (0,0), the control latch is programmed. Table 7 shows the input data format for programming the control latch.

Power-Down

DB21 (PD2) and DB20 (PD1) provide programmable power-down modes.

In the programmed asynchronous power-down, the device powers down immediately after latching a 1 into Bit PD1, with the condition that PD2 has been loaded with a 0. In the programmed synchronous power-down, the device power-down is gated by the charge pump to prevent unwanted frequency jumps. Once the power-down is enabled by writing a 1 into Bit PD1 (on the condition that a 1 has also been loaded to PD2), the device goes into power-down on the second rising edge of the R counter output, after LE goes high. When the CE pin is low, the device is immediately disabled regardless of the state of PD1 or PD2.

When a power-down is activated (either synchronous or asynchronous mode), the following events occur:

- All active dc current paths are removed.
- The R, N, and timeout counters are forced to their load state conditions.
- The charge pump is forced into three-state mode.
- The digital lock detect circuitry is reset.
- The RF outputs are debiased to a high impedance state.
- The reference input buffer circuitry is disabled.
- The input register remains active and capable of loading and latching data.

Charge Pump Currents

CPI3, CPI2, and CPI1 in the ADF4360 family determine Current Setting 1.

CPI6, CPI5, and CPI4 determine Current Setting 2. See the truth table in Table 7.

Output Power Level

Bits PL1 and PL2 set the output power level of the VCO. See the truth table in Table 7.

Mute-Till-Lock Detect

DB11 of the control latch in the ADF4360 family is the Mute-Till-Lock Detect bit. This function, when enabled, ensures that the RF outputs are not switched on until the PLL is locked.

CP Gain

DB10 of the control latch in the ADF4360 family is the Charge Pump Gain bit. When it is programmed to 1, Current Setting 2 is used. When it is programmed to 0, Current Setting 1 is used.

Charge Pump Three-State

This bit puts the charge pump into three-state mode when programmed to a 1. It should be set to 0 for normal operation.

Phase Detector Polarity

The PDP bit in the ADF4360 family sets the phase detector polarity. The positive setting enabled by programming a 1 is used when using the on-chip VCO with a passive loop filter or with an active noninverting filter. It can also be set to 0, which is required if an active inverting loop filter is used.

MUXOUT Control

The on-chip multiplexer is controlled by M3, M2, and M1. See the truth table in Table 7.

Counter Reset

DB4 is the counter reset bit for the ADF4360 family. When this is 1, the R counter and the A, B counters are reset. For normal operation, this bit should be 0.

Core Power Level

PC1 and PC2 set the power level in the VCO core. The recommended setting is 5 mA. See the truth table in Table 7.

N COUNTER LATCH

Table 8 shows the input data format for programming the N counter latch.

Reserved Bits

DB2 to DB7 are spare bits and have been designated as Reserved. They should be programmed to 0.

B Counter Latch

B13 to B1 program the B counter. The divide range is 3 (00.....0011) to 8191 (11....111).

Overall Divide Range

The overall VCO feedback divide range is defined by B.

CP Gain

DB21 of the N counter latch in the ADF4360 family is the charge pump gain bit. When this is programmed to 1, Current Setting 2 is used. When programmed to 0, Current Setting 1 is used. This bit can also be programmed through DB10 of the control latch. The bit always reflects the latest value written to it, whether this is through the control latch or the N counter latch.

R COUNTER LATCH

With (C2, C1) = (0, 1), the R counter latch is programmed. Table 9 shows the input data format for programming the R counter latch.

R Counter

R1 to R14 set the counter divide ratio. The divide range is 1 (00......001) to 16383 (111......111).

Antibacklash Pulse Width

DB16 and DB17 set the antibacklash pulse width.

Lock Detect Precision

DB18 is the lock detect precision bit. This bit sets the number of reference cycles with less than 15 ns phase error for entering the locked state. With LDP at 1, five cycles are taken; with LDP at 0, three cycles are taken.

Test Mode Bit

DB19 is the test mode bit (TMB) and should be set to 0. With TMB = 0, the contents of the test mode latch are ignored and normal operation occurs as determined by the contents of the control latch, R counter latch, and N counter latch. Note that test modes are for factory testing only and should not be programmed by the user.

Band Select Clock

These bits set a divider for the band select logic clock input. The output of the R counter is by default the value used to clock the band select logic, but if this value is too high (>1 MHz), a divider can be switched on to divide the R counter output to a smaller value (see Table 9).

Reserved Bits

DB23 to DB22 are spare bits that have been designated as Reserved. They should be programmed to 0.

CHOOSING THE CORRECT INDUCTANCE VALUE

The ADF4360-8 can be used at many different frequencies simply by choosing the external inductors to give the correct output frequency. Figure 21 shows a graph of both minimum and maximum frequency versus the external inductor value. The correct inductor should cover the maximum and minimum frequencies desired. The inductors used are 0603 CS or 0805 CS type from Coilcraft. To reduce mutual coupling, the inductors should be placed at right angles to one another.

The lowest center frequency of oscillation possible is approximately 65 MHz, which is achieved using 560 nH inductors. This relationship can be expressed by

$$F_O = \frac{1}{2\pi\sqrt{9.3 \text{ pF}(0.9 \text{ nH} + L_{EXT})}}$$

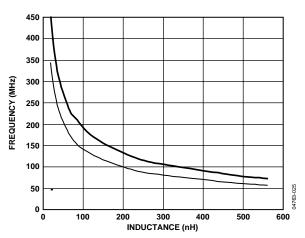


Figure 21. Output Center Frequency vs. External Inductor Value

Where F_O is the center frequency and L_{EXT} is the external inductance. The approximate value of capacitance at the midpoint of the center band of the VCO is 9.3 pF, and the approximate value of internal inductance due to the bond wires is 0.9 nH. The VCO sensitivity is a measure of the frequency change versus the tuning voltage. It is a very important parameter for the low-pass filter. Figure 22 shows a graph of the tuning sensitivity (in MHz/V) versus the inductance (nH). It can be seen that as the inductance increases, the sensitivity decreases. This relationship can be derived from the equation above, i.e., since the inductance has increased, the change in capacitance from the varactor has less of an effect on the frequency.

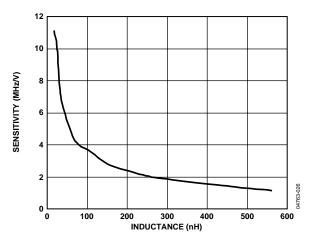


Figure 22. Tuning Sensitivity (in MHz/V) vs. Inductance (nH)

FIXED FREQUENCY LO

Figure 23 shows the ADF4360-8 used as a fixed frequency LO at 200 MHz. The low-pass filter was designed using ADIsimPLL for a channel spacing of 2 MHz and an open-loop bandwidth of 100 kHz. The maximum PFD frequency of the ADF4360-8 is 8 MHz. Since using a larger PFD frequency allows the use of a smaller N, the in-band phase noise is reduced to as low as possible, –109 dBc/Hz. The typical rms phase noise (100 Hz to 100 kHz) of the LO in this configuration is 0.09°. The reference frequency is from a 16MHz TCXO from Fox; thus, an R value of 2 is programmed. Taking into account the high PFD frequency and its effect on the band select logic, the band select clock divider is enabled. In this case, a value of 8 is chosen. A very simple shunt inductor and dc blocking capacitor complete the RF output stage.

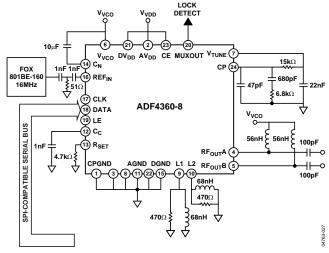


Figure 23. Fixed Frequency LO

POWER-UP

After power-up, the part needs three writes for normal operation. The correct sequence is to the R counter latch, followed by the control latch, and N counter latch.

INTERFACING

The ADF4360 family has a simple SPI® compatible serial interface for writing to the device. CLK, DATA, and LE control the data transfer. When LE goes high, the 24 bits that have been clocked into the appropriate register on each rising edge of CLK are transferred to the appropriate latch. See Figure 2 for the timing diagram and Table 5 for the latch truth table.

The maximum allowable serial clock rate is 20 MHz. This means that the maximum update rate possible is 833 kHz or one update every 1.2 μ s. This is certainly more than adequate for systems that have typical lock times in hundreds of microseconds.

ADuC812 Interface

Figure 24 shows the interface between the ADF4360 family and the ADuC812 MicroConverter®. Since the ADuC812 is based on an 8051 core, this interface can be used with any 8051-based microcontrollers. The MicroConverter is set up for SPI master mode with CPHA = 0. To initiate the operation, the I/O port driving LE is brought low. Each latch of the ADF4360 family needs a 24-bit word, which is accomplished by writing three 8-bit bytes from the MicroConverter to the device. After the third byte has been written, the LE input should be brought high to complete the transfer.

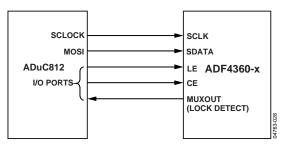


Figure 24. ADuC812 to ADF4360-x Interface

I/O port lines on the ADuC812 are also used to control power-down (CE input) and detect lock (MUXOUT configured as lock detect and polled by the port input). When operating in the described mode, the maximum SCLOCK rate of the ADuC812 is 4 MHz. This means that the maximum rate at which the output frequency can be changed is 166 kHz.

ADSP-2181 Interface

Figure 25 shows the interface between the ADF4360 family and the ADSP-21xx digital signal processor. The ADF4360 family needs a 24-bit serial word for each latch write. The easiest way to accomplish this using the ADSP-21xx family is to use the autobuffered transmit mode of operation with alternate framing. This provides a means for transmitting an entire block of serial data before an interrupt is generated.

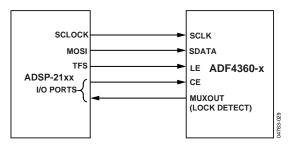


Figure 25. ADSP-21xx to ADF4360-x Interface

Set up the word length for 8 bits and use three memory locations for each 24-bit word. To program each 24-bit latch, store the 8-bit bytes, enable the autobuffered mode, and write to the transmit register of the DSP. This last operation initiates the autobuffer transfer.

PCB DESIGN GUIDELINES FOR CHIP SCALE PACKAGE

The leads on the chip scale package (CP-24) are rectangular. The printed circuit board pad for these should be 0.1 mm longer than the package lead length and 0.05 mm wider than the package lead width. The lead should be centered on the pad to ensure that the solder joint size is maximized.

The bottom of the chip scale package has a central thermal pad. The thermal pad on the printed circuit board should be at least as large as this exposed pad. On the printed circuit board, there should be a clearance of at least 0.25 mm between the thermal pad and the inner edges of the pad pattern to ensure that shorting is avoided.

Thermal vias may be used on the printed circuit board thermal pad to improve thermal performance of the package. If vias are used, they should be incorporated into the thermal pad at 1.2 mm pitch grid. The via diameter should be between 0.3 mm and 0.33 mm, and the via barrel should be plated with 1 ounce of copper to plug the via.

The user should connect the printed circuit thermal pad to AGND. This is internally connected to AGND.

OUTPUT MATCHING

There are a number of ways to match the output of the ADF4360-8 for optimum operation; the most basic is to use a 50 Ω resistor to $V_{\rm VCO}.$ A dc bypass capacitor of 100 pF is connected in series as shown in Figure 26. Because the resistor is not frequency dependent, this provides a good broadband match. The output power in the circuit below typically gives -9 dBm output power into a 50 Ω load.

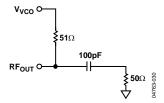


Figure 26. Simple ADF4360-8 Output Stage

A better solution is to use a shunt inductor (acting as an RF choke) to V_{VCO} . This gives a better match and, therefore, more output power.

Experiments have shown that the circuit shown in Figure 27 provides an excellent match to 50 Ω over the operating range of the ADF4360-8. This gives approximately 0 dBm output power across the specific frequency range of the ADF4360-8 using the recommended shunt inductor, followed by a 100 pF dc blocking capacitor.

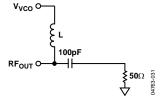


Figure 27. Optimum ADF4360-8 Output Stage

The recommended value of this inductor changes with the VCO center frequency. A graph of the optimum inductor value versus frequency is shown in Figure 28.

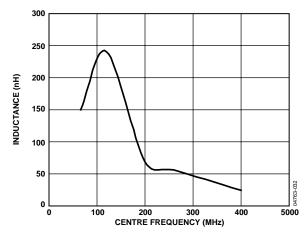
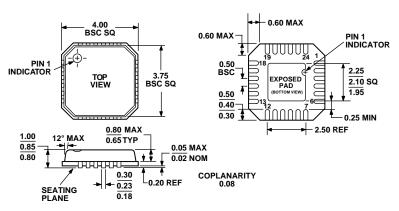


Figure 28. Optimum ADF4360-8 Shunt Inductor

Both complementary architectures can be examined using the EVAL-ADF4360-8EB1 evaluation board. If the user does not need the differential outputs available on the ADF4360-8, the user should either terminate the unused output or combine both outputs using a balun. Alternatively, instead of the LC balun, both outputs may be combined using a 180° rat-race coupler.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-220-VGGD-2

Figure 29. 24-Lead Lead Frame Chip Scale Package [LFCSP] 4 mm × 4 mm Body (CP-24-1) Dimensions shown in millimeters

ORDERING GUIDE

| Model | Temperature Range | Frequency Range | Package Option |
|-------------------|-------------------|-------------------|------------------|
| ADF4360-8BCP | −40°C to +85°C | 65 MHz to 400 MHz | CP-24-1 |
| ADF4360-8BCPRL | -40°C to +85°C | 65 MHz to 400 MHz | CP-24-1 |
| ADF4360-8BCPRL7 | −40°C to +85°C | 65 MHz to 400 MHz | CP-24-1 |
| EVAL-ADF4360-8EB1 | | | Evaluation Board |

NOTES

| ADF4360-8 |
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| NOTES |
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